



# YJF15G15A

## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

$V_{DS}$	150V
$I_D$	15A
$R_{DS(ON)}$ ( at $V_{GS}=10V$ )	70m
$R_{DS(ON)}$ ( at $V_{GS}=6V$ )	80m
100% EAS Tested	
100% $V_{DS}$ Tested	

### General Description

gate trench MOSFET technology  
 $R_{DS(on)}$  & FOM  
 Excellent stability and uniformity  
 -0 Flammability Rating  
 Free

### Applications

gement

### Absolute Maximum Ratings ( $T_A=25$ unless otherwise noted)

Parameter		Symbol	Limit	Units
Drain-source Voltage		$V_{DS}$	150	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25$	$I_D$	4	A
	$T_A=100$		2.5	
	$T_C=25$		15	
	$T_C=100$		9.5	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	40	A
Avalanche energy <sup>B</sup>		EAS	4.4	mJ
Total Power Dissipation <sup>C</sup>	$T_A=25$	$P_D$	2.5	W
	$T_A=100$		1	
	$T_C=25$		41	
	$T_C=100$		16	

Junction and Storage Temperature Range

$T_J, T_{STG}$

-55 +150



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## Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D$	150	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=150V, V_{GS}=0V$	-	-	1	
		$V_{DS}=150V, V_{GS}=0V, T_J=150$	-	-	100	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}= \pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}= V_{GS}, I_D$	2	3	4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=15A$	-	50	70	
		$V_{GS}=6V, I_D=10A$	-	55	80	
Diode Forward Voltage	$V_{SD}$	$I_S=15A, V_{GS}=0V$	-	0.95	1.3	V
Gate resistance	$R_G$	$f=1MHz$	-	1.5	-	
Maximum Body-Diode Continuous Current	$I_S$		-	-	15	A
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=75V, V_{GS}=0V, f=1MHz$	-	785	-	pF
Output Capacitance	$C_{oss}$		-	55	-	
Reverse Transfer Capacitance	$C_{rss}$		-	4	-	
<b>Switching Parameters</b>						
Total Gate Charge	$Q_g$	$V_{GS}=10V, V_{DS}=75V, I_D=7.5A$	-	18	-	nC
Gate-Source Charge	$Q_{gs}$		-	5	-	
Gate-Drain Charge	$Q_{gd}$		-	4.5	-	
Reverse Recovery Charge	$Q_{rr}$	$I_F=7.5A, di/dt=100A/us$	-	179	-	nC
Reverse Recovery Time	$t_{rr}$		-	53	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=75V, I_D=7.5A$ $R_{GEN}=2.2$	-	12	-	ns
Turn-on Rise Time	$t_r$		-	5	-	
Turn-off Delay Time	$t_{D(off)}$		-	39	-	
Turn-off fall Time	$t_f$		-	6	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B.  $T_J=25$ ,  $V_{DD}=50V, V_G=10V, R_G$  0.5mH,  $I_{AS}=4.2A$ .

C.  $P_g$  is based on max. junction temperature, using junction-case thermal resistance.

D. The value of  $R$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in the still air environment with  $T_A=25$ . The maximum allowed junction temperature of 150. The value in any given application depends on the user's specific board design.



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## Typical Electrical and Thermal Characteristics Diagrams

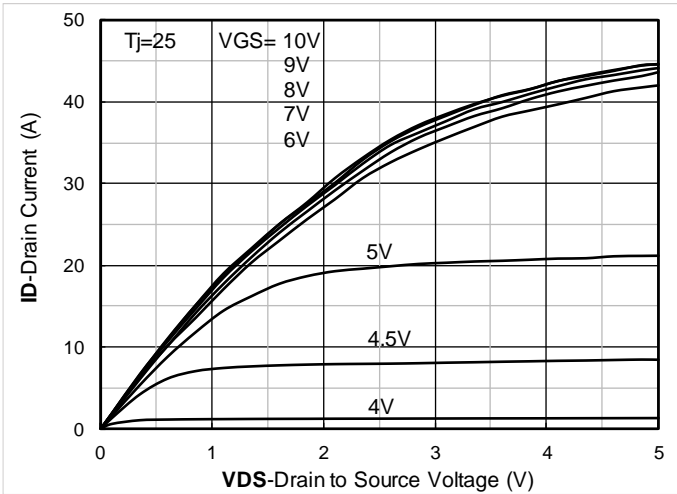


Figure 1. Output Characteristics

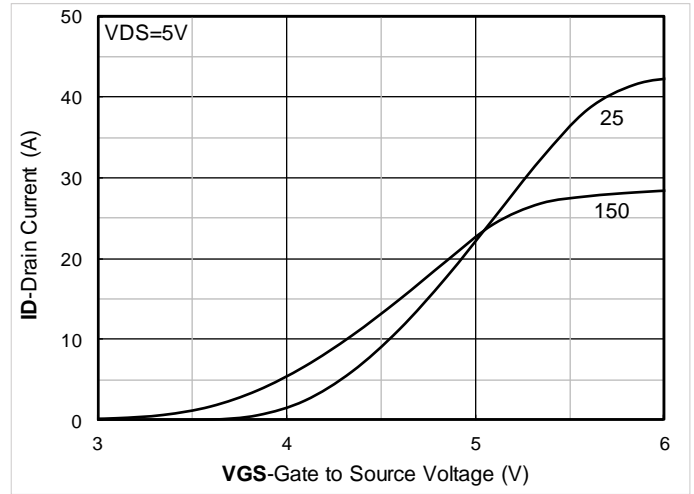


Figure 2. Transfer Characteristics

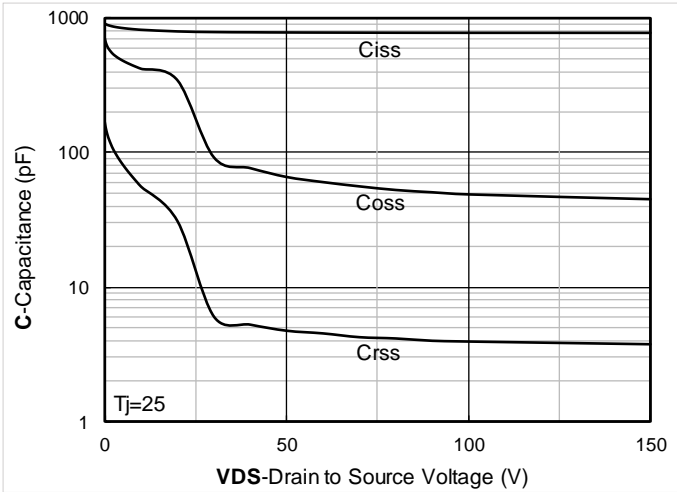


Figure 3. Capacitance Characteristics

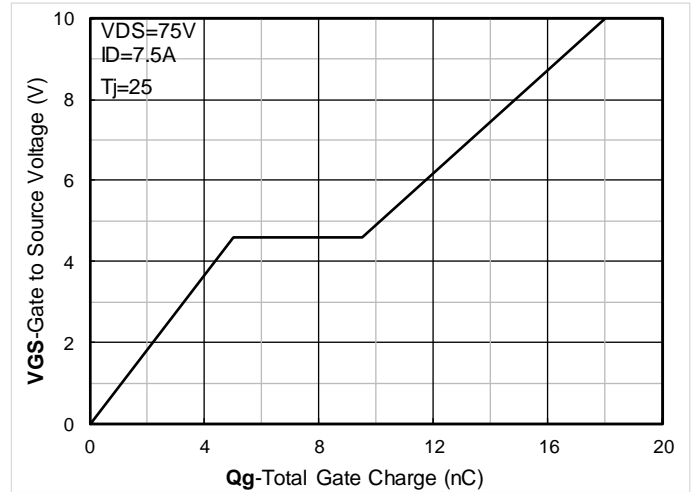


Figure 4. Gate Charge

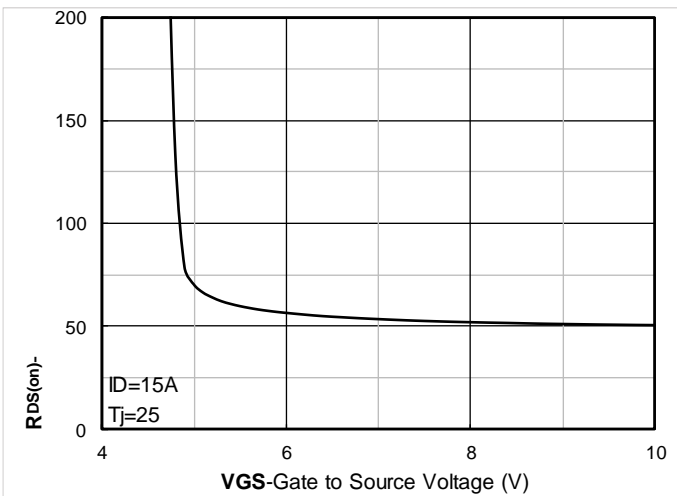


Figure 5. On-Resistance vs Gate to Source Voltage

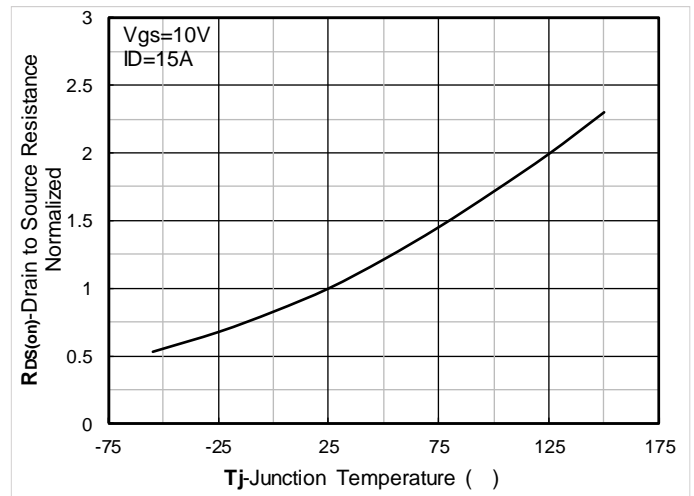


Figure 6. Normalized On-Resistance



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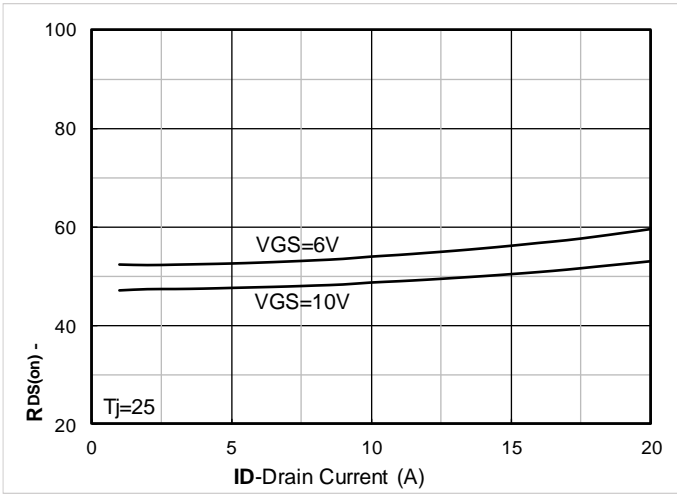


Figure 7. RDS(on) VS Drain Current

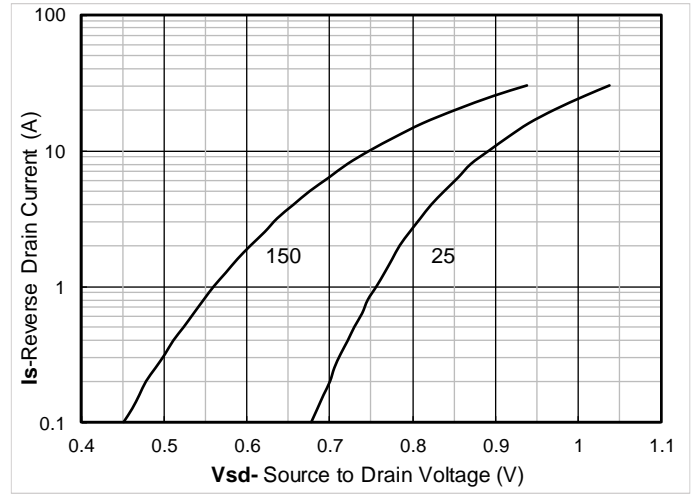


Figure 8. Forward characteristics of reverse diode

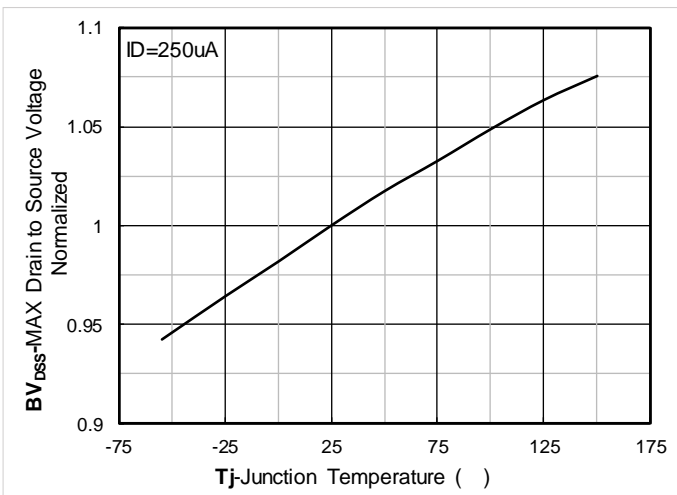


Figure 9. Normalized breakdown voltage

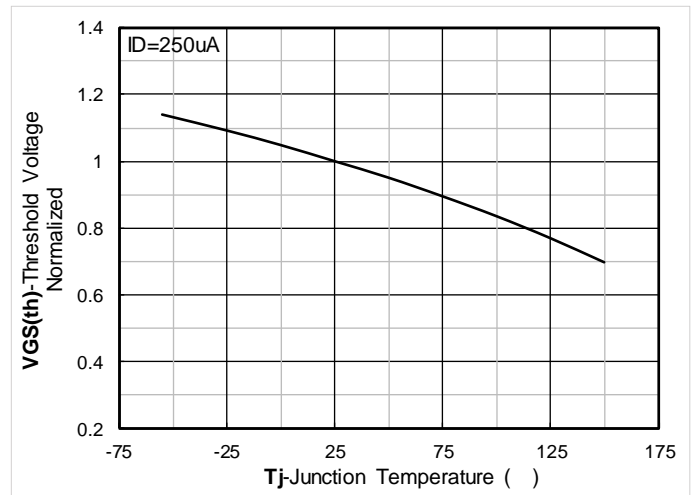


Figure 10. Normalized Threshold voltage

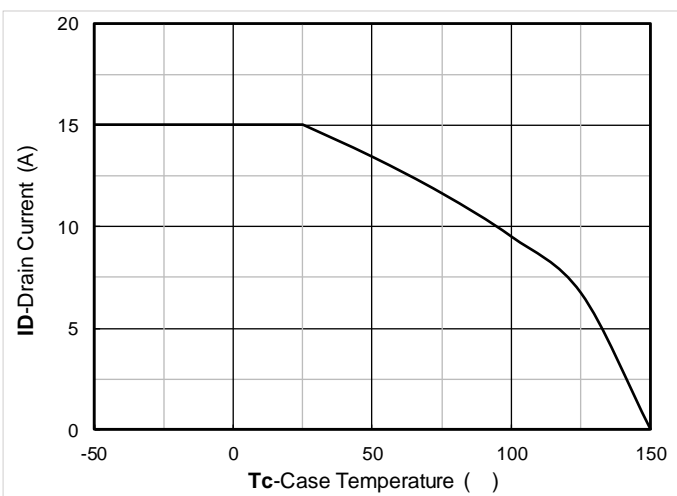


Figure 11. Current dissipation

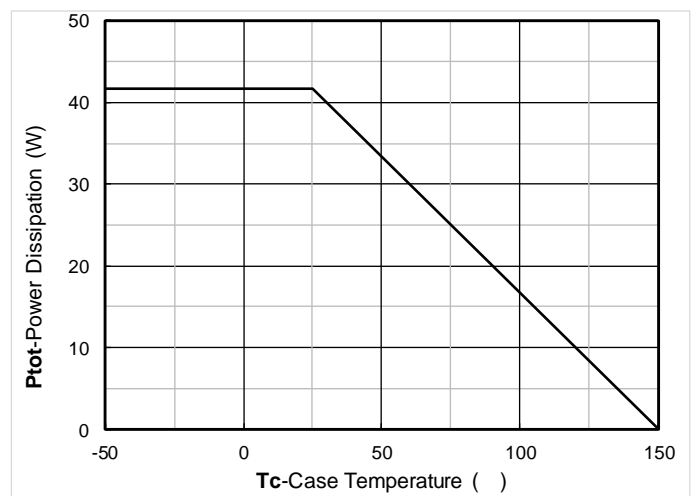


Figure 12. Power dissipation



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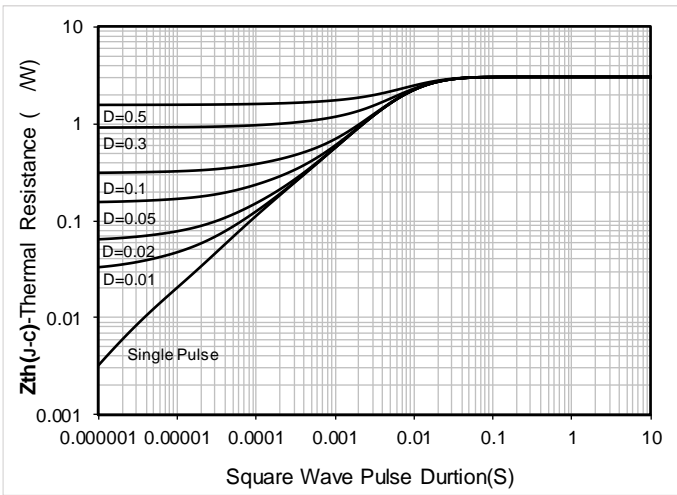


Figure 13. Maximum Transient Thermal Impedance

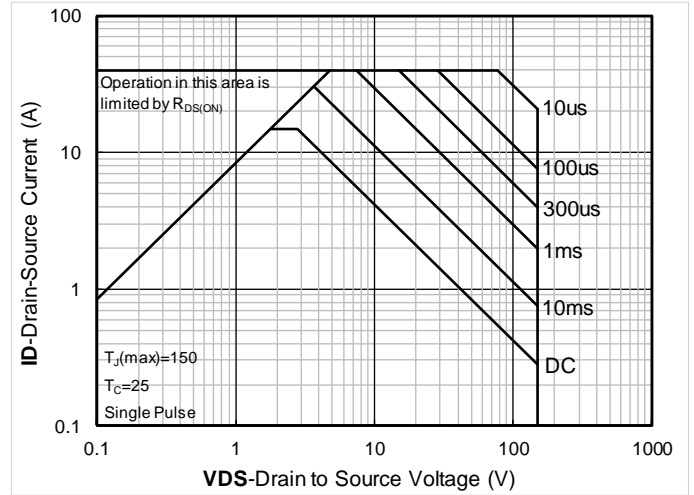


Figure 14. Safe Operation Area

## Test Circuits & Waveforms

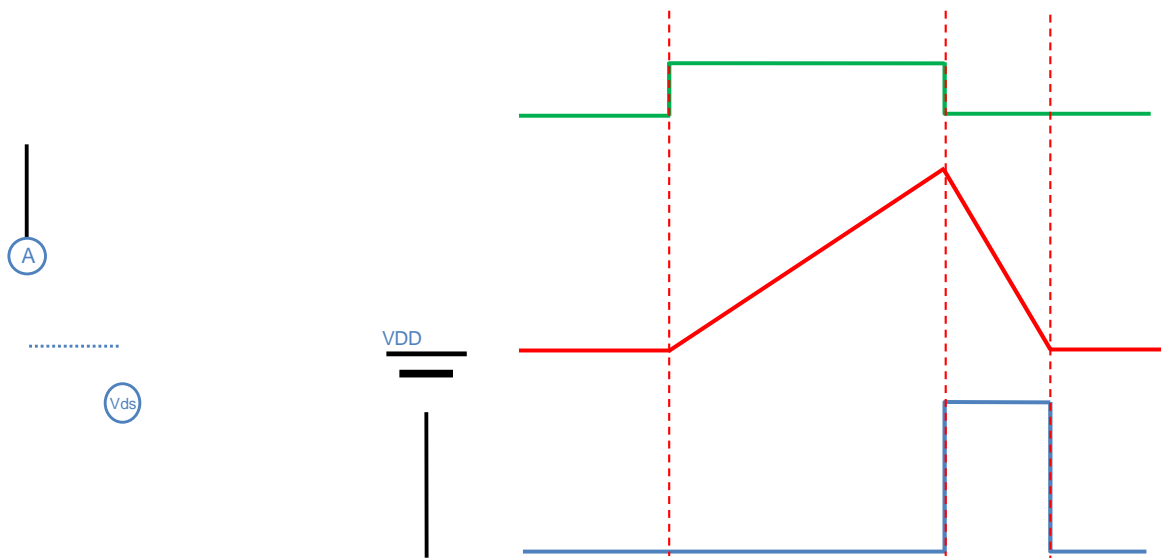


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



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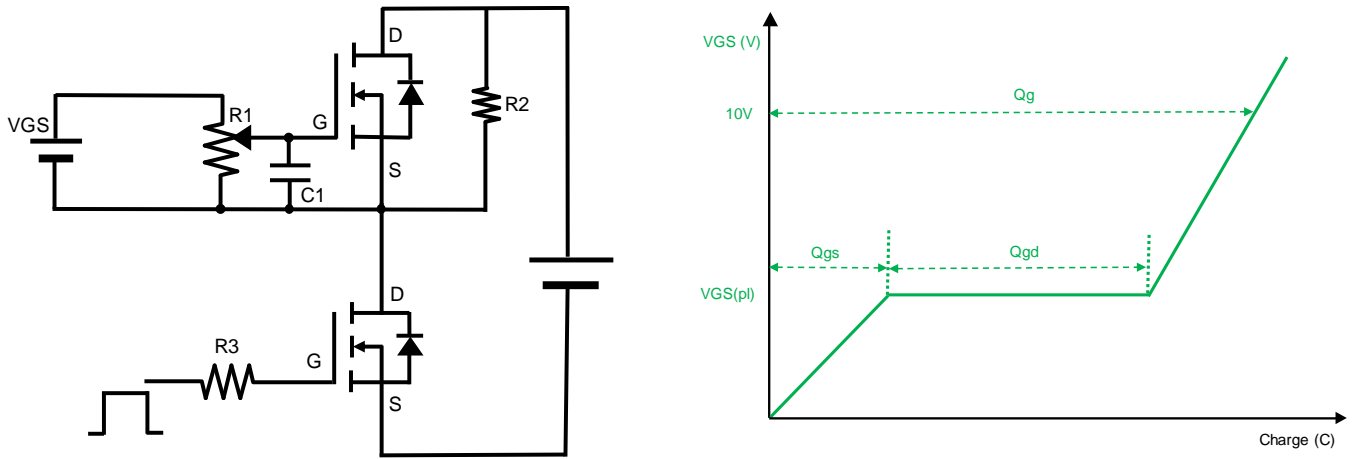


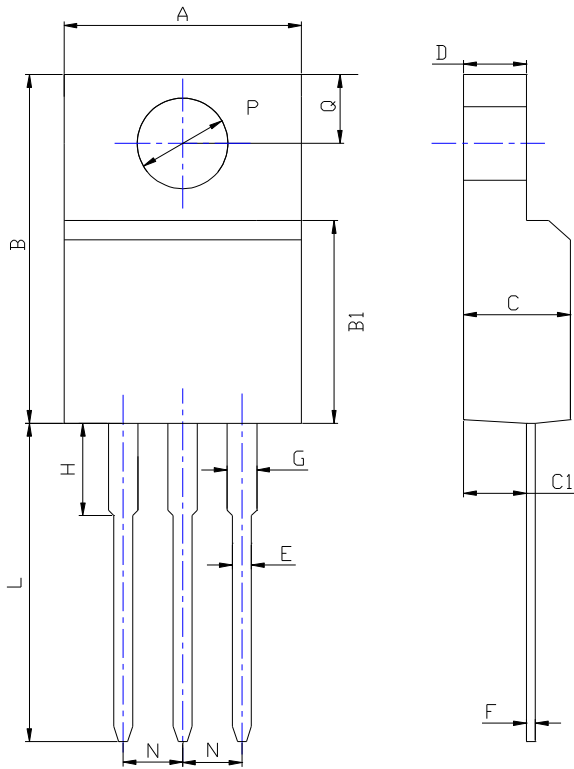
Figure B.12.2.1 Gate Charge Test Circuit & Waveform

45 10eW\* r2.8m0 g0 GUS



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## ITO-220AB-B Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.382	0.406	9.700	10.300
B	0.610	0.634	15.500	16.100
B1	0.354	0.370	8.990	9.390
C	0.173	0.189	4.400	4.800
C1	0.085	0.100	2.150	2.550
D	0.098	0.114	2.500	2.900
E	0.028	0.035	0.700	0.900
F	0.016	0.024	0.400	0.600
G	0.044	0.056	1.120	1.420
H	0.134	0.150	3.400	3.800
L	0.496	0.535	12.600	13.600
N	0.092	0.108	2.340	2.740
Q	0.124	0.140	3.150	3.550
P	0.118	0.130	3.000	3.300

**NOTE:**

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.



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